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(54) **SENSING PRODUCT AND METHOD OF MAKING**

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H01L 31/18 (2006.01)

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CPC **H01L 31/0232** (2013.01); **H01L 31/101** (2013.01); **H01L 31/18** (2013.01)

(58) **Field of Classification Search**
CPC H01L 27/1464
USPC 438/56, 57, 66, 70, 71, 73
See application file for complete search history.

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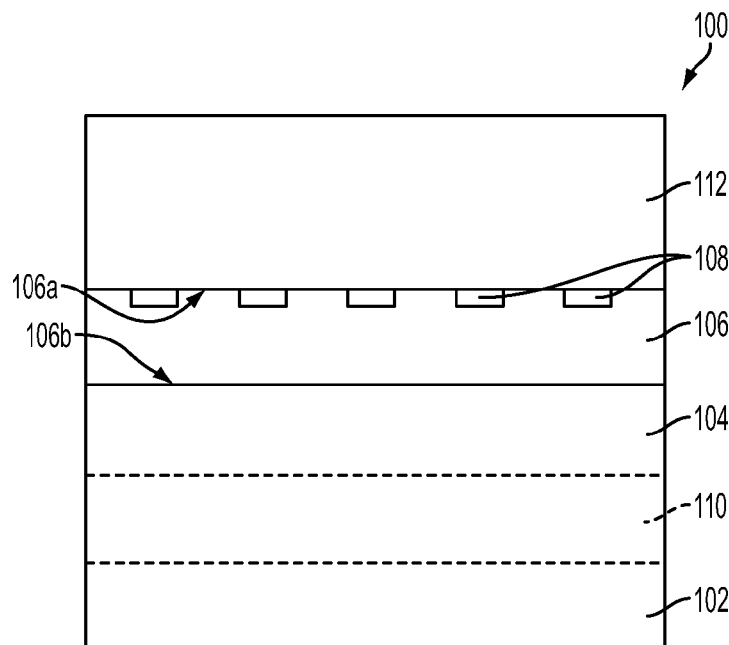
Assistant Examiner — Erik T Peterson

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(57) **ABSTRACT**

This description relates to a sensing product formed using a substrate with a plurality of epi-layers. At least a first epi-layer has a different composition than the composition of a second epi-layer. The sensing product optionally includes at least one radiation sensing element in the second epi-layer and optionally an interconnect structure over the second epi-layer. The sensing product is formed by removing the substrate and all epi-layers other than the second epi-layer. A light incident surface of the second epi-layer has a total thickness variation of less than about 0.15 μm .

11 Claims, 4 Drawing Sheets



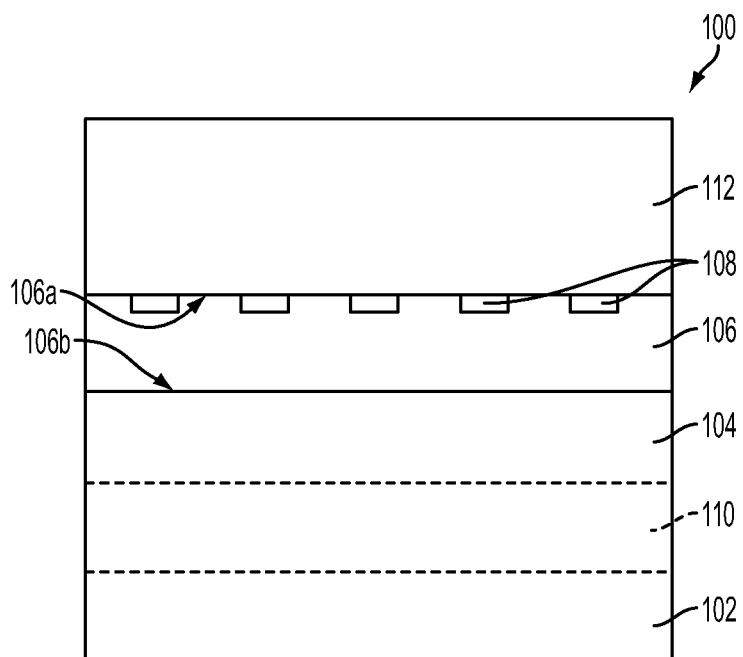


FIG. 1

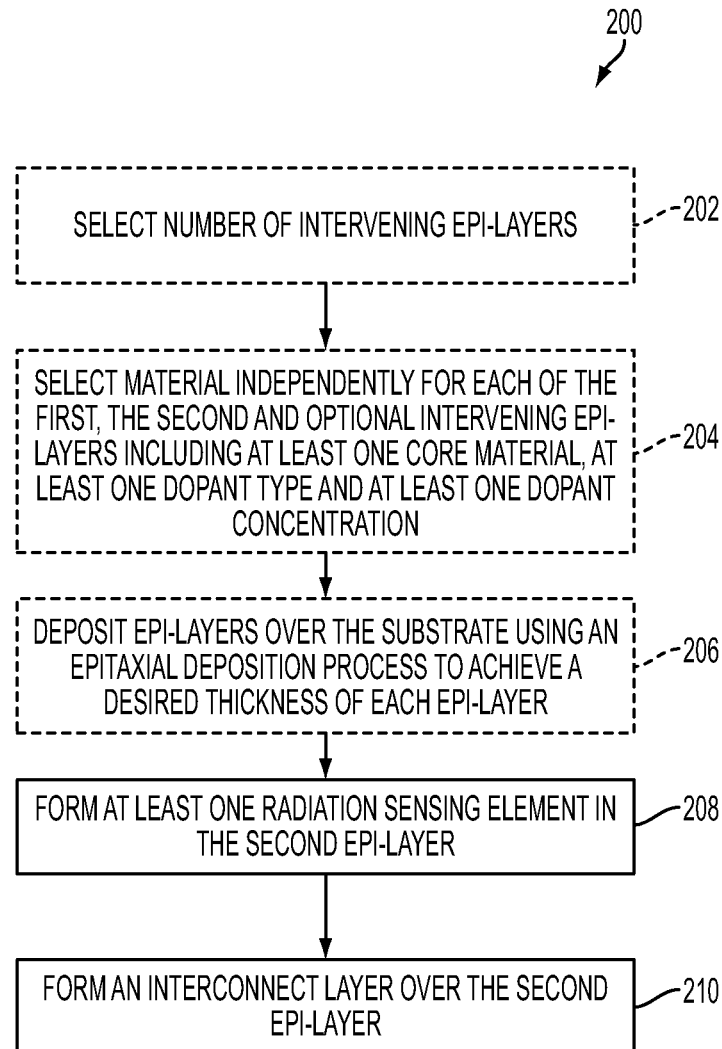


FIG. 2

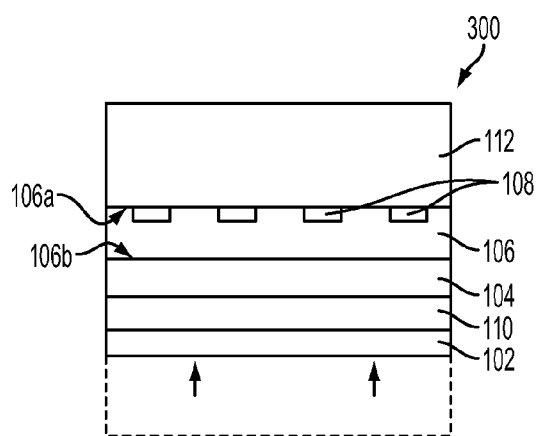


FIG. 3A

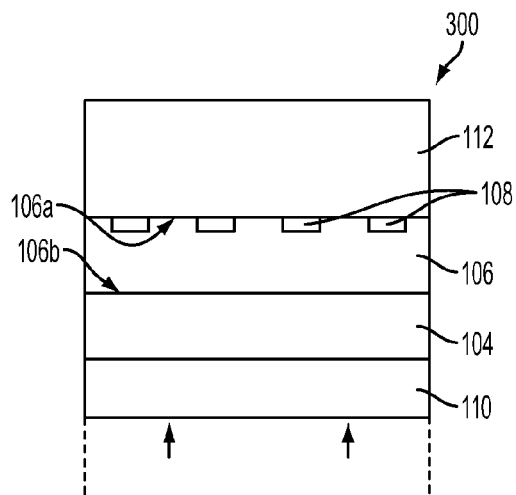


FIG. 3B

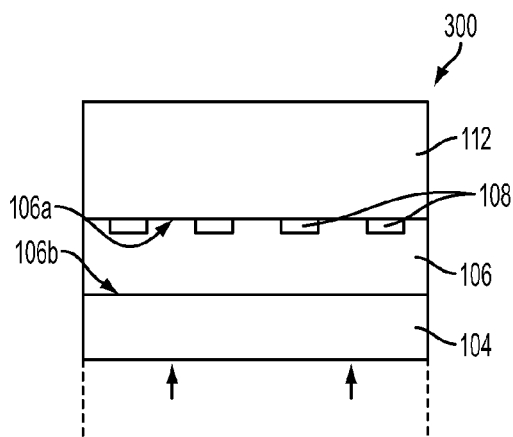


FIG. 3C

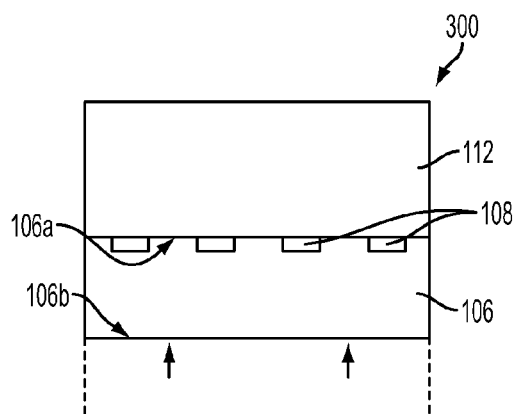


FIG. 3D

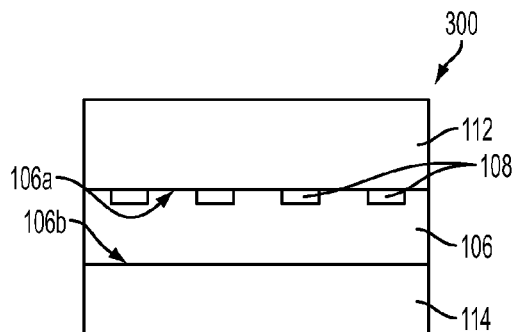


FIG. 3E

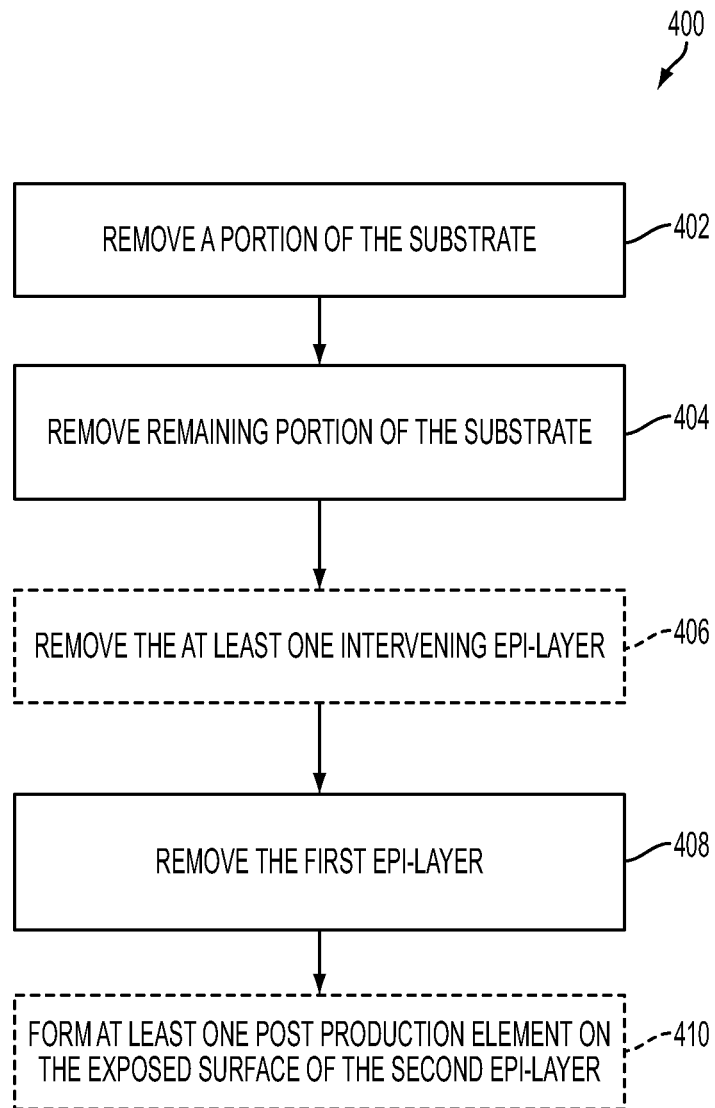


FIG. 4

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SENSING PRODUCT AND METHOD OF MAKING

BACKGROUND

Sensing products are used in a variety of camera arrangements, including backside illumination sensors, and are sometimes used in low light environments. Several sensing products rely on passing light through a semiconductor layer for sensing incident light. The semiconductor layer is thin enough to allow light to propagate, however, some techniques of layer thinning create a semiconductor layer having a significant thickness variation across the layer. Variations in the layer's thickness result in uneven propagation of light through the semiconductor layer, which in turn prevents the sensor from collecting accurate data resulting in decreased image clarity.

A total thickness variation of the light incident surface for the sensing product resulting from some techniques produces image distortion in an image captured by the sensing product. Some techniques create a total thickness variation of a light incident surface of 0.20 μm or greater. As the total thickness variation increases, the amount of image distortion increases.

BRIEF DESCRIPTION OF THE DRAWINGS

One or more embodiments are illustrated by way of example, and not by limitation, in the figures of the accompanying drawings, wherein elements having the same reference numeral designations represent like elements throughout. It is emphasized that, in accordance with standard practice in the industry various features may not be drawn to scale and are used for illustration purposes only. In fact, the dimensions of the various features in the drawings may be arbitrarily increased or reduced for clarity of discussion.

FIG. 1 is a side view of an intermediate product of a sensing product according to some embodiments;

FIG. 2 is a flowchart of a method of making the intermediate product of FIG. 1, according to some embodiments;

FIGS. 3A-3E are side views of a sensing product during various stages of development according to some embodiments; and

FIG. 4 is a flowchart of a method of making a sensing product, according to some embodiments.

DETAILED DESCRIPTION

The following disclosure provides many different embodiments, or examples, for implementing different features of the invention. Specific examples of components and arrangements are described below to simplify the present disclosure. These are of course, merely examples and are not intended to be limiting.

FIG. 1 is a side view of an intermediate product 100 of a backside illumination sensor according to some embodiments. The intermediate product 100 includes a substrate 102. A first epi-layer 104 is over the substrate 102. The intermediate product also includes a second epi-layer 106 over the substrate 102. In some embodiments, optional radiation sensing elements 108 are in the second epi-layer 106, and in some embodiments, an optional interconnect structure 112 is over the second epi-layer 106 and electrically connected to the radiation sensing elements 108. In some embodiments a single optional intervening epi-layer 110 is between the first epi-layer 104 and the substrate 102. In some embodiments, a plurality of optional intervening epi-layers is between the first

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epi-layer 104 and the substrate 102. In other embodiments, the intermediate product 100 does not comprise an intervening epi-layer.

The first epi-layer 104 is the closest epi-layer to the second epi-layer 106. The second epi-layer 106 has a different composition than the composition of the first epi-layer 104. Each of the first epi-layer 104 and the second epi-layer 106 independently comprises at least one core material and optionally at least one dopant. In some embodiments, the second epi-layer 106 has a different at least one core material than the at least one core material of the first epi-layer 104. In some embodiments, the second epi-layer 106 has a different at least one dopant than the at least one dopant of the first epi-layer 104.

In some embodiments, the total thickness variation of the second epi-layer 106 is less than about 0.15 μm . This range, in some embodiments, is narrower, e.g., from 0.1 μm to 0.15 μm . In some embodiments, the second epi-layer 106 has a total thickness variation ranging from about 6% of the thickness of the second epi-layer 106 to about 10% of the thickness of the second epi-layer 106. This range, in some embodiments, is narrower, e.g., from 6% of the thickness of the second epi-layer 106 to 10% of the thickness of the second epi-layer 106. In some embodiments, the total thickness variation is measured using a metrology tool to measure the thickness of the second epi-layer at various points across a surface of the second epi-layer prior to forming the backside illumination sensor. The thickness of the second epi-layer 106 is measured from interface 106a, the interface furthest from the substrate 102, to the opposite interface 106b, the interface closest to the substrate 102. The difference between the maximum thickness measured and the minimum thickness measured is the total thickness variation. A total thickness variation less than or equal to about 0.15 μm makes it possible to reduce the amount of distortion of light passing through the second epi-layer 106.

In some embodiments, the substrate 102 comprises at least one core material and optionally at least one dopant. The at least one core material, in some embodiments, comprises silicon, germanium, carbide, oxide, gallium arsenide, indium phosphate or another suitable material. In some embodiments, the substrate is an alloy. In some embodiments, the substrate 102 is a non-conductive material. In some embodiments, the substrate 102 is a conductive material or semi-conductive material. In some embodiments, the substrate is p-doped or n-doped (i.e., positive doped or negative doped). The at least one dopant, in some embodiments, includes boron, aluminum, gallium, indium, or other suitable materials.

In some embodiments, the thicknesses of first epi-layer 104 and second epi-layer 106 are independently less than 5.0 μm . In some embodiments, the thicknesses of the first epi-layer 104 and the second epi-layer 106 independently range from about 1.0 μm to about 2.2 μm . This range, in some embodiments, is narrower, e.g., from 1.0 μm to 2.2 μm . In some embodiments, the thicknesses of the first epi-layer 104 and the second epi-layer 106 differ. In some embodiments, the thicknesses of the first epi-layer 104 and the second epi-layer 106 are measured using the same metrology tool used to measure the total thickness variation of the second epi-layer. In other embodiments, the thicknesses of the first epi-layer 104 and the second epi-layer 106 are measured using a different metrology tool.

The first epi-layer 104, the second epi-layer 106 and the at least one intervening layer 110 independently comprise at least one core material and optionally at least one dopant. The at least one core material, in some embodiments, indepen-

dently comprises silicon, germanium, carbide, oxide, gallium arsenide, indium phosphate or another suitable material. In some embodiments, the first epi-layer **104**, the second epi-layer **106** and the at least one intervening layer **110** are independently an alloy or non-alloy. In some embodiments, the first epi-layer **104**, the second epi-layer **106** and the at least one intervening layer **110** are independently a non-conductive material, a conductive or a semi-conductive material. In some embodiments, the first epi-layer **104**, the second epi-layer **106** and the at least one intervening layer **110** independently are p-doped or n-doped. The at least one dopant, in some embodiments, includes boron, aluminum, gallium, indium, or other suitable materials.

In some embodiments, the substrate **102**, the first epi-layer **104**, the second epi-layer **106** and the at least one intervening layer **110** have the same at least one core material. In some embodiments, the substrate **102**, the first epi-layer **104**, the second epi-layer **106** and the at least one intervening layer **110** have different at least one core materials. In some embodiments, some of the substrate **102**, the first epi-layer **104**, the second epi-layer **106** and the at least one intervening layer **110** have the same at least one core material, and some of the substrate **102**, the first epi-layer **104**, the second epi-layer **106** and the at least one intervening layer **110** have different at least one core materials.

In some embodiments, the first epi-layer **104** and the second epi-layer **106** are independently n-doped or p-doped. The at least one dopants, in some embodiments, are independently chosen from those identified above. In some embodiments, the type of dopant, i.e., negative dopant or positive dopant, is different for the first epi-layer **104** than the second epi-layer **106**.

In some embodiments, the dopant concentrations in the substrate **102**, the first epi-layer **104**, second epi-layer **106** and at least one intervening epi-layer **110** independently range from about 10^{14} atoms/cm³ to about 10^{20} atoms/cm³. This range, in some embodiments, is narrower, e.g., from 10^{14} atoms/cm³ to 10^{20} atoms/cm³.

In some embodiments, the n-dopant concentrations in the substrate **102**, the first epi-layer **104**, second epi-layer **106** and at least one intervening epi-layer **110** independently range from about 10^{14} atoms/cm³ to about 10^{16} atoms/cm³. This range, in some embodiments, is narrower, e.g., from 10^{14} atoms/cm³ to 10^{16} atoms/cm³.

In some embodiments, the p-dopant concentrations independently range from about 10^{14} atoms/cm³ to about 10^{16} atoms/cm³. This range, in some embodiments, is narrower, e.g., from 10^{14} atoms/cm³ to 10^{16} atoms/cm³.

In some embodiments, the substrate **102**, the first epi-layer **104**, second epi-layer **106** and at least one intervening epi-layer **110** have the same dopant concentration. In some embodiments, the substrate **102**, the first epi-layer **104**, second epi-layer **106** and at least one intervening epi-layer **110** have different dopant concentrations.

In some embodiments, the at least one intervening epi-layer **110** comprises silicon. In some embodiments, the at least one intervening epi-layer **110** is p-doped silicon or n-doped silicon. For each intervening epi-layer, suitable dopants, in some embodiments, are independently chosen from those identified above.

In some embodiments, the first epi-layer **104** is p-doped silicon, the second epi-layer **106** is n-doped silicon and the at least one intervening layer **110** is n-doped silicon. In other embodiments, the first epi-layer **104** is n-doped silicon, the second epi-layer **106** is p-doped silicon and the at least one intervening layer **110** is p-doped silicon.

In some embodiments, the substrate **102** has opposite doping type (n-dopant or p-dopant) to the doping type of the first epi-layer **104** or the at least one intervening epi-layer **110**. In other embodiments, the substrate **102** has the same doping type as the doping type of the first epi-layer **104** or the at least one intervening epi-layer **110**. In some embodiments, the substrate **102** is p-doped, the at least one intervening layer **110** is n-doped, the first epi-layer **104** is p-doped and the second epi-layer **106** is n-doped. In some embodiments, the substrate **102** is n-doped, the at least one intervening layer **110** is p-doped, the first epi-layer **104** is n-doped and the second epi-layer **106** is p-doped. In some embodiments without at least one intervening layer **110**, the substrate **102** is p-doped, the first epi-layer **104** is n-doped and the second epi-layer **106** is p-doped. In some embodiments without at least one intervening layer **110**, the substrate **102** is n-doped, the first epi-layer **104** is p-doped and the second epi-layer **106** is n-doped.

In the embodiment of FIG. 1, the intermediate product **100** includes optional radiation sensing elements **108** to detect incident light. In some embodiments, the radiation sensing elements **108** are photodiodes. In some embodiments, the radiation sensing elements **108** are photogates, reset transistors, source follower transistors, transfer transistor, or other suitable light detecting elements. In some embodiments, the intermediate product **100** comprises a plurality of radiation sensing elements **108**. In some embodiments, the intermediate product **100** comprises a single radiation sensing element. In some embodiments, the intermediate product **100** comprises an array of radiation sensing elements **108**.

Interconnect structure **112** includes lines and vias configured to electrically connect to the radiation sensing elements **108**. In some embodiments, the lines are metal lines. In some embodiments, interconnect structure **112** further includes additional circuitry configured to analyze the signals from the at least one radiation sensing element **108**.

The intermediate product **100** is subject to multiple uses. In some embodiments, the intermediate product **100** is used to form a sensing product, e.g., an optical sensor, suitable for use in a detector or a camera. These and other products, e.g., a backside illumination sensor, comprise the second epi-layer **106** optionally having a total thickness variation less than or equal to about 0.15 μ m, which makes it possible to reduce the amount of distortion of light passing through the second epi-layer **106**. If the sensing product is in a camera, using epi-layer **106** makes it possible to produce higher resolution images than light in a camera having an incident surface having a larger total thickness variation.

In some embodiments, the sensing product comprises the second epi-layer **106**, the at least one radiation sensing element **108** and the interconnect structure **112**, wherein the second epi-layer **106** is configured to receive and transmit incident light. In some embodiments, the sensing product is the intermediate product **100**, with the substrate **102**, the first epi-layer **104** and any of the at least one intervening epi-layer **110** removed. In some embodiments, the sensing product has a light incident surface corresponding to the surface **106b** of the second epi-layer **106**.

The total thickness variation of the sensing product permits more even light propagation through the second epi-layer **106** and to the at least one radiation sensing element **108** than some techniques. The more even propagation of light makes it possible to achieve better performance of the sensing product and higher quality images are obtainable from the sensing product.

In some embodiments, the sensing product includes additional post-production elements, such a color filter, a micro-

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lens, an antireflective coating, a buffer layer, or other suitable elements formed over surface **106b** of the second epi-layer **106**.

FIG. 2 depicts a flow chart of a method **200** of making the intermediate product **100**. Method **200** includes forming at least one radiation sensing element **108** in the second epi-layer **106** and forming the interconnect structure **112** over the second epi-layer **106** to electrically connect to the at least one radiation sensing element **108**.

Method **200** begins with optional step **202**, in which a number of the at least one intervening epi-layer **110** is selected. The intermediate product **100** of FIG. 1, e.g., includes a single intervening epi-layer **110**.

Method **200** continues with optional step **204**, in which the materials for the epi-layers are selected. The material selection includes selection of the at least one core material and optionally the at least one dopant. The at least one core material and the at least one dopant are selected from those discussed above. The material selection step further includes selecting the dopant type (e.g., n-type or p-type) and concentration.

In optional step **206**, the at least one intervening epi-layer **110**, the first epi-layer **104** and the second epi-layer **106** are formed over substrate **102** using an epitaxial deposition process. In some embodiments, the epitaxial deposition process is vapor-phase. In other embodiments, the epitaxial deposition process is liquid-phase or solid-phase. The epitaxial deposition process comprises depositing a crystalline layer over a surface by adsorbing atoms or molecules onto the surface. The deposition process continues until the epi-layer reaches a desired thickness.

Method **200** continues with step **208**, in which the at least one radiation sensing element **108** is formed in surface **106a** of the second epi-layer **106**. In some embodiments, the at least one radiation sensing element **108** is formed by ion implantation. In some embodiments, etching trenches into the second epi-layer **106** and filling the trenches with radiation sensing material to form at least one radiation sensing element **108**. In some embodiments, the at least one radiation sensing element **108** is formed by depositing radiation sensing material on surface **106a** and heating to diffuse the radiation sensing material in the second epi-layer **106**. In some embodiments, the radiation sensing material includes silicon, germanium, indium gallium arsenide, lead sulfide, or other suitable materials.

In some embodiments, isolation features are formed between radiation sensing elements **108**. In some embodiments, isolation features are formed by etching a trench in the second epi-layer **106** and filling the trench with dielectric material.

In step **210**, interconnection layer **112** is formed over surface **106a** of the second epi-layer **106** to provide an electrical connection to the at least one radiation sensing element **108**. In some embodiments, depositing a dielectric layer, etching openings and forming lines and vias, forms interconnection layer **112**. Other methods of forming interconnection layer **112** would be recognizable by one of ordinary skill in the art.

FIGS. 3A-3E are diagrams of a side view of a sensing product **300** at various stages of development according to some embodiments. Elements of the sensing product **300** are similar to the elements of the intermediate product **100**. In the embodiment of FIGS. 3A-3E, the substrate **102** comprises p-doped silicon; the at least one intervening layer **110** comprises n-doped silicon, the first epi-layer **104** comprises p-doped silicon and the second epi-layer **106** comprises n-doped silicon. In some embodiments, other at least one core material and at least one dopant are independently selected

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for the substrate **102**, the at least one intervening layer **110**, the first epi-layer **104** and the second epi-layer **106**.

FIG. 4 depicts a flow chart for a method **400** of making sensing product **300** according to some embodiments. Method **400** includes removing the substrate **102** from the intermediate product **100** and thereafter removing the first epi-layer **104** to expose the surface **106b** of the second epi-layer **106**.

Method **400** begins with step **402**, in which a portion of the substrate **102** is removed. In some embodiments, the substrate **102** is removed using a grinding process. The grinding process includes using a grinding wheel to remove a portion of the substrate **102**.

The remaining portion of the substrate **102** is removed in step **404**. In some embodiments, the remaining portion of the substrate **102** is removed using an etching process. In some embodiments, the etching process is a selective etching process. In some embodiments, the grinding of step **402** is continued until substantially all of the substrate **102** is removed. In the embodiment of FIGS. 3A-3E, the substrate **102** is p-doped silicon and etching includes a wet etching process contacting an aqueous solution comprising hydrofluoric acid, nitric acid, and acetic acid (HNA) with the substrate **102**. In the embodiment of FIGS. 3A-3E, the at least one intervening epi-layer **110** is n-doped silicon. HNA etches the p-doped silicon of substrate **102** at a much higher rate than the n-doped silicon of the at least one intervening epi-layer **110**. In some embodiments, other selective etching etchants are selected based upon the composition, including at least one core material and the at least one dopant, of the substrate **102**, the optional at least one intervening layer **110**, the first epi-layer **104** and the second epi-layer **106**. Following step **404**, the substrate **102** is substantially or entirely removed.

In some embodiments, when the composition, including the at least one core material and the at least one dopant, for the substrate **102** is the same as the composition of the at least one intervening epi-layer **110**, the selective etching process is continued to remove the at least one intervening epi-layer **110** as well as the substrate **102**. In some embodiments, when the composition of the first epi-layer **104** is the same as the composition of the at least one intervening epi-layer **110** and the composition of the substrate **102**, the selective etching process is continued to remove the first epi-layer **104**, the at least one intervening epi-layer **110** and the substrate **102**.

In the embodiment of FIGS. 3A-3E, the at least one intervening epi-layer **110** is removed in step **406**. In some embodiments, the at least one intervening epi-layer **110** is removed using chemical and mechanical planarization. In other embodiments, the at least one intervening epi-layer **110** is removed using a selective etching process or another process. Chemical and mechanical planarization (CMP) uses a carrier wafer to securely hold the sensing product **300** in contact with a pad on a platen. The platen and the carrier are rotated to strip the portion of the sensing product **300** contacting the pad. In some embodiments, a polishing slurry or other polishing solution is added to the pad to assist in the removal process. The polishing slurry or other polishing solution are selected based on the material removed during the CMP process. Following step **406**, substantially all of or the entire at least one intervening epi-layer **110**.

In step **408**, the first epi-layer **104** is removed. In some embodiments, the first epi-layer **104** is removed using selective etching. In other embodiments, the first epi-layer **104** is removed using chemical and mechanical planarization or other suitable material removal processes. In the embodiments of FIGS. 3A-3E, the first epi-layer **104** is p-doped silicon and is selective etched using HNA similar to the etch-

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ing of substrate **102** in step **404**. In some embodiments, other selective etching etchants are selected based upon the composition, including at least one core material and the at least one dopant, of the substrate **102**, the optional at least one intervening layer **110**, the first epi-layer **104** and the second epi-layer **106**. Once the first epi-layer **104** is removed, surface **106b** of the second epi-layer **106** is exposed. At this point a metrology tool is used to measure the total thickness variation of the second epi-layer **106**.

The second epi-layer **106** has a sufficiently small total thickness variation, to effectively propagate light to the radiation sensing elements **108**. In some embodiments, the sufficiently small total thickness variation of the second epi-layer **106** results from the epitaxial deposition process and the highly selective etching of the adjacent layer.

Method **400** optionally continues with step **410**, in which post production elements **114** are attached to the surface **106b** of the second epi-layer **106**. In some embodiments, post production elements include a color filter, a microlens, a protective buffer layer, or other suitable elements.

In some embodiments, the sensing product **300** is a camera, such as a backside illumination sensor.

One aspect of the description relates to a manufacture including a substrate, a first epi-layer, and a second epi-layer, where the second epi-layer had a different material than the first epi-layer.

Another aspect of the description relates to a method of making a semiconductor device comprising in an intermediate product including a substrate, a first epi-layer, and a second epi-layer, where the second epi-layer has a different material than the first epi-layer. The method further includes forming at least one radiation sensing element in the second epi-layer of the intermediate product and forming an interconnect layer over the second epi-layer of the intermediate product to electrically connect with the at least one radiation sensing element.

Still another aspect of the description relates to a method of making a semiconductor device comprising in an intermediate product comprising a substrate, a first epi-layer, a second epi-layer, where the second epi-layer has a different material than the first epi-layer, at least one radiation sensing element in the second epi-layer, and an interconnect layer over the second epi-layer and configured to electrically connect to the at least one radiation sensing element. The method of making the semiconductor device further includes removing the substrate from the intermediate product and thereafter removing the first epi-layer to expose a surface of the second epi-layer.

The above description discloses exemplary steps, but they are not necessarily required to be performed in the order described. Steps can be added, replaced, changed in order, and/or eliminated as appropriate, in accordance with the spirit and scope of embodiment of the disclosure. Embodiments that combine different claims and/or different embodiments are within the scope of the disclosure and will be apparent to those skilled in the art after reviewing this disclosure.

What is claimed is:

1. A method of making a semiconductor device, the method comprising:

forming at least one radiation sensing element in a second epi-layer of an intermediate product, wherein the intermediate product comprises a substrate, a first epi-layer over the substrate and the second epi-layer over the first epi-layer, wherein the second epi-layer has a different composition from the first epi-layer, and the second epi-layer has a doped surface extending across the entire

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second epi-layer in a direction parallel to an interface between the first epi-layer and the substrate;

forming an interconnect layer over the second epi-layer of the intermediate product to electrically connect with the at least one radiation sensing element; and

removing the substrate and the entire first epi-layer to expose the entire doped surface of the second epi-layer.

2. The method of claim 1, wherein the forming the at least one radiation sensing element comprises forming the at least one radiation sensing element in the second epi-layer having a total thickness variation of less than about 0.15 microns (μm).

3. The method of claim 1, wherein the forming the at least one radiation sensing elements comprises at least one of ion implantation, etching a trench, or diffusing a radiation sensing material in the second epi-layer.

4. A method of making a semiconductor device comprising:

forming at least one radiation sensing element in a first epi-layer having a first dopant type, wherein the first epi-layer is over a second epi-layer having a second dopant type and a substrate, wherein the first dopant type is opposite the second dopant type, and the first epi-layer comprises a doped surface extending parallel to an interface between the substrate and the second epi-layer;

forming an interconnect layer over the first epi-layer, the interconnect layer electrically connected with the at least one radiation sensing element;

removing a portion of the substrate using a first process; and

removing the entire second epi-layer using a second process different from the first process, wherein removing the second epi-layer comprises exposing the entire doped surface of the first epi-layer having a total thickness variation of less than about 0.15 microns (μm), and the doped surface extends across every radiation sensing element of the at least one radiation sensing element.

5. The method of claim 4, wherein removing the second epi-layer using the second process comprises removing a portion of the substrate using the second process.

6. The method of claim 5, wherein removing the second epi-layer using the second process comprises removing the second epi-layer using a grinding or planarization process.

7. The method of claim 5, wherein removing the second epi-layer using the second process comprises removing the second epi-layer using a selective etching process.

8. The method of claim 4, wherein forming the at least one radiation sensing element in the first epi-layer comprises forming the at least one radiation sensing element in the first epi-layer comprising a silicon core material, and the second epi-layer comprises the silicon core material.

9. The method of claim 4, wherein forming the at least one radiation sensing element comprises forming a plurality of radiation sensing elements.

10. The method of claim 4, wherein forming the at least one radiation sensing element in the first epi-layer comprises forming the at least one radiation sensing element in the first epi-layer having a dopant concentration ranging from about 10^{14} atoms/ cm^3 to about 10^{20} atoms/ cm^3 .

11. The method of claim 4, wherein forming the at least one radiation sensing element in the first epi-layer comprises forming the at least one radiation sensing element in the first epi-layer having a first dopant concentration, and the second epi-layer has a second dopant concentration different from the first dopant concentration.

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